NSN 5961-00-415-2016

Transistor - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5961-00-415-2016

Inclosure Material:

Metal

Overall Length:

1.003 inches

Overall Height:

0.330 inches

Overall Width:

0.505 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

600.0 breakdown voltage, collector-to-base, emitter open and 600.0 breakdown voltage, collector-to-emitter, with specified resistance between base and emitter and 5.0 breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

6.00 microamperes zero-gate-voltage source current preset

Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Precious Material And Location:

Terminal surfaces gold

Precious Material:

Gold

Test Data Document:

00752-334761 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

3 uninsulated wire lead and 1 case

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0